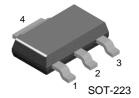


September 2006

NZT902 NPN Low Saturation Transistor

· These devices are designed with high current gain and low saturation voltage with collector currents up to 3A continuous.



1. Base 2. Collector 3. Emitter

Absolute Maximum Ratings* Ta=25°C unless otherwise noted

Symbol	Parameter	Value	Units
V _{CEO}	Collector-Emitter Voltage	90	V
V _{CBO}	Collector-Base Voltage	120	V
V _{EBO}	Emitter-Base Voltage	5	V
I _C	Collector Current - Continuous	3	А
T_J	Junction Temperature	150	°C
T _{STG}	Storage Temperature Range	- 55 ~ +150	°C

^{*} These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

Thermal Characteristics* $T_a=25$ °C unless otherwise noted

Symbol	Parameter	Value	Units
P_D	Total Device Dissipation	1	W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	125	°C/W

^{*} Device mounted on FR-4 PCB 36 mm X 18 mm X 1.5 mm.

Electrical Characteristics* T_a = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Units
BV _{CEO}	Collector-Emitter Breakdown Voltage	I _C = 10mA	90			V
BV _{CBO}	Collector-Base Breakdown Voltage	I _C = 100μA	120			V
BV _{EBO}	Emitter-Base Breakdown Voltage	$I_{E} = 100 \mu A$	5			V
I _{CBO}	Collector-Base Cutoff Current	V _{CB} = 100V V _{CB} = 100V, Ta = 100 °C			100 10	nA uA
I _{EBO}	Emitter-Base Cutoff Current	V _{EB} = 4V			100	nA
h _{FE}	DC Current Gain	$I_{C} = 0.1A, V_{CE} = 2V$ $I_{C} = 1A, V_{CE} = 2V$ $I_{C} = 2A, V_{CE} = 2V$	80 80 25			
V _{CE(sat)}	Collector-Emitter Saturation Voltage	$I_C = 0.1A, I_B = 5.0mA$ $I_C = 1A, I_B = 100mA$ $I_C = 3A, I_B = 300mA$			50 250 600	mV mV mV
V _{BE(sat)}	Base-Emitter Saturation Voltage	I _C = 1A, I _B = 100mA			1.25	V
C _{obo}	Output Capacitance	$V_{CB} = 10V, I_E = 0, f = 1MHz$			35	pF
f _T	Transition Frequency	$I_C = 100 \text{mA}, V_{CE} = 5 \text{V}, f = 100 \text{MHz}$	75			MHz

^{*} Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2.0%

¹⁾ These ratings are based on a maximum junction temperature of 150°C.
2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Typical Performance Characteristics

Figure 1. Static Characteristic

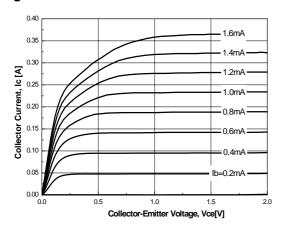


Figure 2. DC current Gain

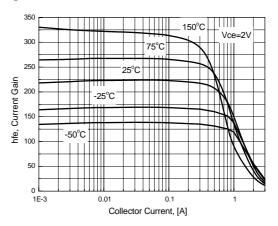


Figure 3. Collector-Emitter Saturation Voltage

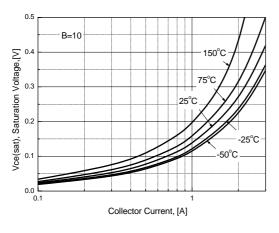


Figure 4. Base-Emitter Saturation Voltage

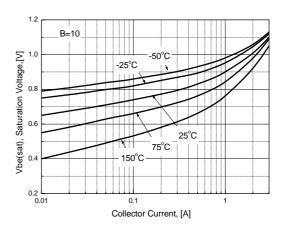


Figure 5. Output Capacitance

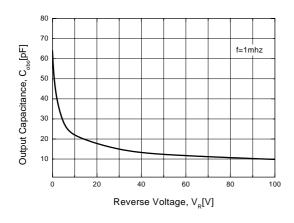
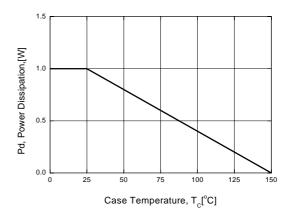


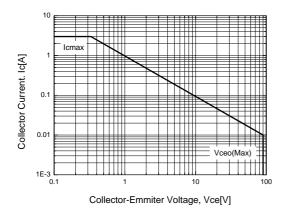
Figure 6. Power Dissipation vs
Ambient Temperature



2

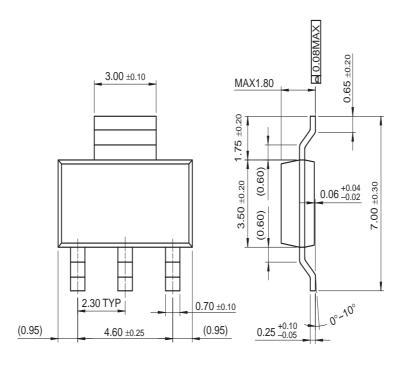
Typical Performance Characteristics

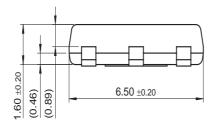
Figure 9. SOA



Mechanical Dimensions

SOT-223





Dimensions in Millimeters

UltraFET® UniFET™ VCX™ Wire™

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